Am27X020

Advanced Micro Devices

2 Megabit (262,144 x 8-Bit) CMOS ExpressROM Device

DISTINCTIVE CHARACTERISTICS

- As an OTP EPROM alternative:
 - Factory optimized programming
 - Fully tested and guaranteed
- As a Mask ROM alternative:
 - Shorter leadtime
 - Lower volume per code
- Fast access time
 - 75 ns
- Single +5 V power supply
- Compatible with JEDEC-approved EPROM pinout
- ±10% power supply tolerance

- High noise immunity
- Low power dissipation
 - 100 µA maximum CMOS standby current
- Available in Plastic Dual In-Line Package (PDIP),
 Plastic Leaded Chip Carrier (PLCC), and
 Thin Small Outline Package (TSOP)
- Latch-up protected to 100 mA from -1 V to Vcc +1 V
- Versatile features for simple interfacing
 - Both CMOS and TTL input/output compatibility
 - Two line control functions

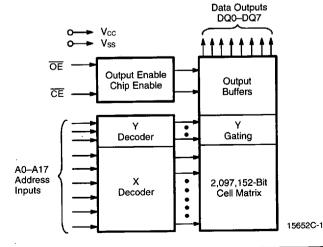
GENERAL DESCRIPTION

The Am27X020 is a factory programmed and tested OTP EPROM. It is programmed after packaging prior to final test. Every device is rigorously tested under AC and DC operating conditions to your stable code. It is organized as 262,144 by 8 bits and is available in plastic dual in-line (PDIP), plastic leaded chip carrier (PLCC), and thin small outline (TSOP) packages. ExpressROM devices provide a board-ready memory solution for medium to high volume codes with short leadtimes. This offers manufacturers a cost-effective and flexible alternative to OTP EPROMs and mask programmed ROMs.

Access times as fast as 75 ns allow operation with highperformance microprocessors with reduced WAIT states. The Am27X020 offers separate Output Enable (OE) and Chip Enable (CE) controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMD's CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 100 mW in active mode, and 100 μ W in standby mode.

BLOCK DIAGRAM



Publication# 15652 Rev. C Amendment/0 Issue Date: May 1995

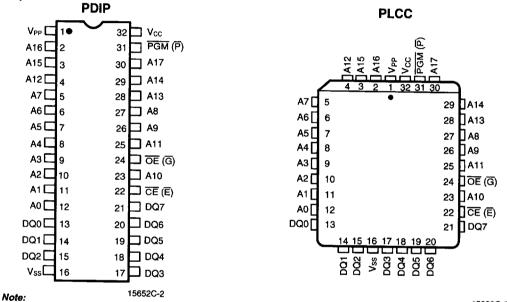
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PRODUCT SELECTOR GUIDE

Family Part No.				Am27X020		
Ordering Part No: Vcc ±5%						-255
V _{CC} ±10%	-75	-90	-120	-150	-200	-
Max Access Time (ns)	70	90	120	150	200	250
CE (E) Access (ns)	70	90	120	150	200	250
OE (G) Access (ns)	40	50	50	65	75	100

CONNECTION DIAGRAMS

Top View



1. JEDEC nomenclature is in parentheses.

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TSOP* A11 □ 0 32 ŌĒ 2 3 A9 🗆 31 30 A10 A8 [CE A13 □ 4 5 29 28 DQ7 A14 □ DQ₆ A17 6 27 DQ5 PGM □ 26 DQ4 8 Vcc □ 25 DQ3 Vpp 24 ٧ss A16 □ 10 23 DQ2 A15 □ 11 22 DQ1 A12 12 DQ0 A7 🗆 13 20 Α0 14 A6 🗆 19 **A**1 **A5** 15 18 A2 A4 C АЗ

*Contact local AMD sales office for package availability

Am27X020

Standard Pinout

4-67

15652C-4

15652C-3

PIN DESIGNATIONS

A0-A17 = Address Inputs CE (E)

= Chip Enable Input DQ0-DQ7 = Data Inputs/Outputs

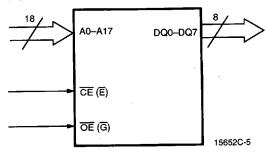
= No External Connection (Do Not Use) DU

= No Internal Connection NC \overline{OE} (\overline{G}) = Output Enable Input = Program Enable Input PGM (P) = Vcc Supply Voltage Vcc

= Program Voltage Input V_{PP}

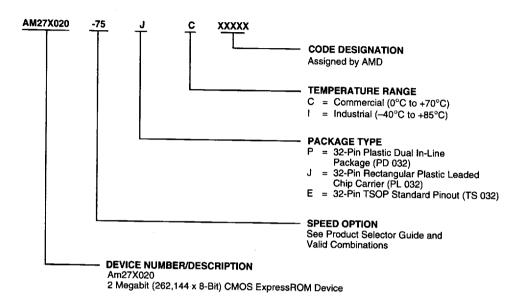
= Ground V_{SS}

LOGIC SYMBOL



ORDERING INFORMATION Standard Products

AMD standard products are available in several packages and operating ranges. The ordering number (Valid Combination) is formed by a combination of:



Valid Comb	Valid Combinations						
AM27X020-75							
AM27X020-90	7						
AM27X020-120	PC, JC, PI, JI, EC, EI						
AM27X020-150] [0, [
AM27X020-200	7						
AM27X020-255	7						

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

FUNCTIONAL DESCRIPTION Read Mode

The Am27X020 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Output Enable (\overline{OE}) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from \overline{CE} to output (t_{CE}) . Data is available at the outputs t_{OE} after the falling edge of \overline{OE} , assuming that \overline{CE} has been LOW and addresses have been stable for at least t_{ACC} - t_{OE} .

Standby Mode

The Am27X020 has a CMOS standby mode which reduces the maximum V_{CC} current to 100 $\mu A.$ It is placed in CMOS-standby when \overline{CE} is at $V_{CC}\pm0.3$ V. The Am27X020 also has a TTL-standby mode which reduces the maximum V_{CC} current to 1.0 mA. It is placed in TTL-standby when \overline{CE} is at $V_{IH}.$ When in standby mode, the outputs are in a high-impedance state, independent of the \overline{OE} input.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- Low memory power dissipation
- Assurance that output bus contention will not occur

It is recommended that \overline{CE} be decoded and used as the primary device-selecting function, while \overline{OE} be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1 μF ceramic capacitor (high frequency, low inherent inductance) should be used on each device between Vcc and Vss to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on ExpressROM device arrays, a 4.7 μF bulk electrolytic capacitor should be used between Vcc and Vss for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

MODE SELECT TABLE

Mode Pins	CE	ŌĒ	PGM	V _{PP}	Outputs
Read	VIL	VIL	×	X	DOUT
Output Disable	Х	ViH	×	χ .	Hi-Z
Standby (TTL)	ViH	Х	×	Х	Hi-Z
Standby (CMOS)	Vcc ± 0.3 V	Х	Х	Х	Hi-Z

Note:

1. X = Either VIH or VIL



ABSOLUTE MAXIMUM RATINGS

Storage Temperature OTP Products	65°C to +125°C 65°C to +150°C
Ambient Temperature with Power Applied	
Voltage with Respect to V _{SS} All pins except V _{CC}	
Vcc	

Note:

 Minimum DC voltage on input or I/O pins is -0.5 V. During transitions, the inputs may overshoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC voltage on input and I/O pins is Vcc +0.5 V which may overshoot to Vcc +2.0 V for periods up to 20 ns.

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices	
Ambient Temperature (T _A)	0°C to +70°C
Industrial (I) Devices Ambient Temperature (T _A)	
Supply Read Voltages	
Vcc for Am27X020-XX5	+4.75 V to +5.25 V
Vcc for Am27X020-XX0	+4.50 V to +5.50 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified (Notes 1, 2 and 4)

Parameter Symbol	Parameter Description	Test Conditions	Min	Max	Unit
Vон	Output HIGH Voltage	Іон = – 400 μΑ	2.4		V
Vol	Output LOW Voltage	1 _{OL} = 2.1 mA		0.45	V
ViH	Input HIGH Voltage		2.0	V _{CC} + 0.5	V
VIL	Input LOW Voltage		-0.5	+0.8	٧
lu	Input Load Current	V _{IN} = 0 V to +V _{CC}		1.0	μА
lLO	Output Leakage Current	Vout = 0 V to +Vcc		5.0	μА
lcc1	V _{CC} Active Current (Note 3)	CE = V _{1L} , f = 10 MHz, 1 _{OUT} = 0 mA		30	mA
lcc2	V _{CC} TTL Standby Current	CE = V _{IH}		1.0	mA
Іссз	Vcc CMOS Standby Current	CE = V _{CC} ± 0.3 V		100	μΑ

Notes:

- 1. V_{CC} must be applied simultaneously or before V_{PP} , and removed simultaneously or after V_{PP} .
- 2. Caution: The Am27X020 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. I_{CC1} is tested with $\overline{OE} = V_{IH}$ to simulate open outputs.
- Minimum DC Input Voltage is -0.5 V. During transitions, the inputs may overshoot to -2.0 V for periods less than 20 ns. Maximum DC Voltage on output pins is V_{cc} + 0.5 V, which may overshoot to V_{cc} + 2.0 V for periods less than 20 ns.

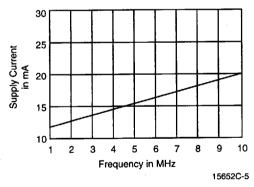


Figure 1. Typical Supply Current vs. Frequency Vcc = 5.5 V, T = 25°C

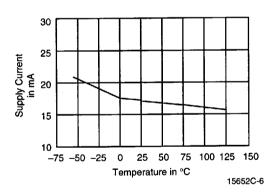


Figure 2. Typical Supply Current vs. Temperature $V_{CC} = 5.5 \text{ V}, f = 10 \text{ MHz}$

CAPACITANCE

Parameter		Test		PD 032		PL 032		TS 032	
Symbol	Parameter Description	Conditions	Тур	Max	Тур	Max	Тур	Max	Unit
CIN	Input Capacitance	Vin = 0	10	12	8	10	10	12	pF
Соит	Output Capacitance	Vout = 0	12	15	9	12	12	14	pF

Notes:

- 1. This parameter is only sampled and not 100% tested.
- 2. TA = +25°C, f = 1 MHz.

SWITCHING CHARACTERISTICS over operating range unless otherwise specified (Notes 1, 3 and 4)

Parameter Symbols						1	Am2	7X020			
JEDEC	Standard	Parameter Description	Test Condition	Test Conditions		-90	-120	-150	-200	-255	Unit
tavqv	tacc	Address to Output Delay	CE = OE = VIL	Min Max	 70	<u> </u>	_ 120	 150			
tELQV	tce	Chip Enable to	OE = VIL	Min		90		150	200 —	250	ns
A.		Output Delay		Max	70	90	120	150	200	250	ns
tGLQV	toe	Output Enable to Output Delay	CE = VIL	Min Max	40	<u>—</u> 50	 50	 65		100	ns
tEHQZ	tor	Chip Enable HIGH or		Min	0	0	0	0	0	0	113
tGHQZ	(Note 2)	Output Enable HIGH, whichever comes first, to Output Float		Max	25	30	30	30	40	60	ns
taxox	tон	Output Hold from		Min	0	0	0	0	0	0	
		Addresses, CE, or OE, whichever occurred first		Max	_		_	_			ns

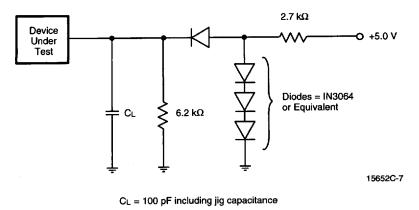
Notes:

- 1. V_{CC} must be applied simultaneously or before V_{PP} , and removed simultaneously or after V_{PP} .
- 2. This parameter is only sampled and not 100% tested.
- 3. Caution: The Am27X020 must not be removed from (or inserted into) a socket or board when VPP or Vcc is applied.
- 4. Output Load: 1 TTL gate and $C_L = 100 pF$

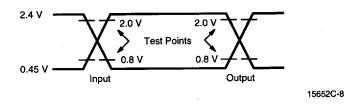
Input Rise and Fall Times: 20 ns Input Pulse Levels: 0.45 V to 2.4 V

Timing Measurement Reference Level: 0.8 V and 2 V for inputs and outputs

SWITCHING TEST CIRCUIT



SWITCHING TEST WAVEFORM



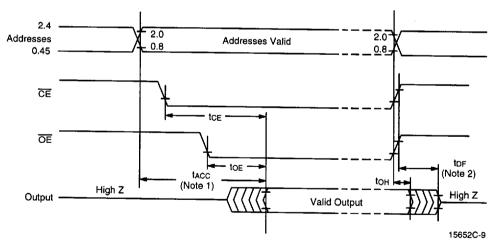
AC Testing: Inputs are driven at 2.4 V for a Logic "1" and 0.45 V for a Logic "0." Input pulse rise and fall times are ≤ 20 ns.

KEY TO SWITCHING WAVEFORMS

WAVEFORM	INPUTS	OUTPUTS
	Must be Steady	Will be Steady
	May Change from H to L	Will be Changing from H to L
	May Change from L to H	Will be Changing from L to H
	Don't Care, Any Change Permitted	Changing, State Unknown
>> -≪	Does Not Apply	Center Line is High- Impedance "Off" State

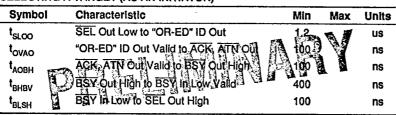
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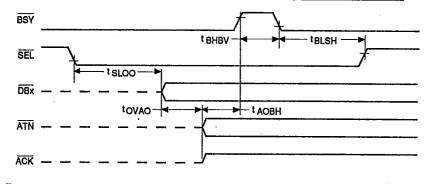
SWITCHING WAVEFORMS



Notes:

- 1. OE may be delayed up to tacc top after the falling edge of the addresses without impact on tacc.
- 2. t_{DF} is specified from \overline{OE} or \overline{CE} , whichever occurs first.

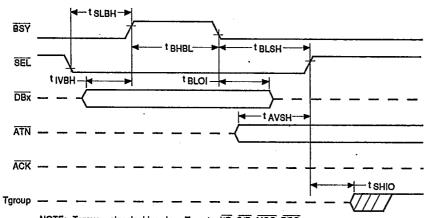




NOTE: Tgroup = signals driven by a Target = I/O, C/D, MSG, REQ

RESPONSE TO SELECTION (AS A TARGET)

Symbol	Characteristic	Min	Max	Units
t _{SLBH}	SEL In Low to BSY In High	A 1		ns
t _{iVBH}	"OR-ED" ID Valid In to BSY In High	A Fig.	A	ns
t _{BHBL}		oly 19.41	200	us
t _{BLOI}	BSY Out Low to "OR-ED." ID Invalid in	0		ns
t _{BLSH}	BSY Out Low to SEL In High	0		ns
tavsh T	ATN Valid In to SEL In High	0		ns
t _{SHIO}	SEL in High to Tgroup Out	100		ns



NOTE: Tgroup = signals driven by a Target = I/O, C/D, MSG, REQ

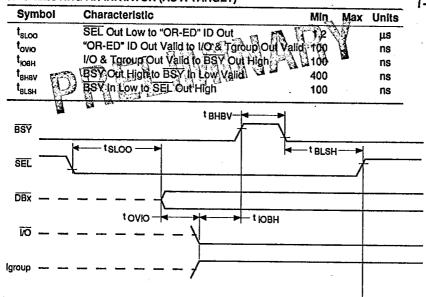
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RESELECTING AN INITIATOR (AS A TARGET)

T-52-33-27



NOTE: Tgroup = signals driven by a Target = $\overline{C/D}$, \overline{MSG} , \overline{REQ} Igroup = signals driven by an Initiator = ATN, ACK

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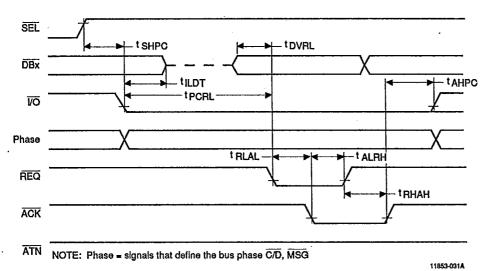
			<u> </u>	TION (AS AN INITIATOR)		
Units	Max	Min		stic	ol Character	Symbol
ns		_ Q_ (to BSY In High		t _{SLBH}
ns	3	(0)	. 64	Valid In to BSY In High		t _{IVBH}
ns		01	MB B	to BSY In High 💢 🐧 🧌	1/O In Low	t _{ILBH}
ns		100°	oup Out	ID Valld , BSY High to Igrou	SEL Low,	t _{BHAO}
ns		100	<i>ऀ</i> ∄ 19 .	Qut to BSY Out Low	Igroup Vali	t _{AVBL}
μs	200	0.4		h to BSY Out Low 1 12	BSY In Hig	t _{BHBL}
ns		0	in	w to "OR-ED" ID Invalid In		t _{BLOI} ,
ns		0		ywtò SEL In High		t _{BLSH}
nş		0		n to BSY Out High	SEA In Hig	t _{shbh}
1 SHBI		SH P	t BLS	1BHBL	1 SLBH	BSY
	- .	<u>*</u> 		1 BLO1	tiven	DBx —
			AVBL	X \		Igroup —
				■ BHAO, I	, icon	1/0
			- tAVBL		t _{ILBH}	_

Tgroup = signals driven by a Target = C/D, MSG, REQ Igroup = signals driven by an Initiator = ATN, ACK *** BSY will still be driven by the reselecting target.

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RECEIVE ASYNCHRONOUS INFORMATION TRANSFER IN (ACTING AS AN INITIATOR)

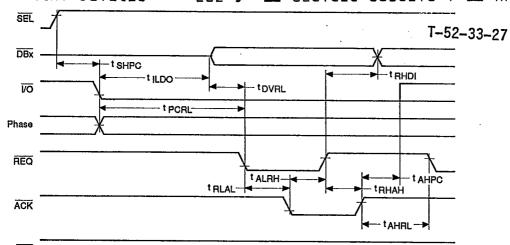
Symbol	Characteristic	Min	Max	Units	T-52-33-27
t _{SHPC}	SEL In High to Phase Change In	0		ns	1-32-33-27
t _{ilDT}	I/O in Low to Data Bus TRISTATE	0	125	ns	
t _{PCRL}	Phase Change In to REQ In Low	13400		ns	
t _{DVRL}	Data Valid In to REQ In Low	\ 0 \ \		ns	
t _{RLAL}	REO In Low to ACK Out Low	0.	175	ns	
t _{ALDI}	ACK Out Low to Data Invalid in	0		ns	
t _{ALRH}	ACK Out Low to REQ In High	0		ns	
t _{RHAH}	REQ In High to ACK Out High	0	175	ns	
tAHPC	ACK Out High to Phase Change In	0		ns	





SEND ASYNCHRONOUS INFORMATION TRANSFER IN (ACTING AS A TARGET)

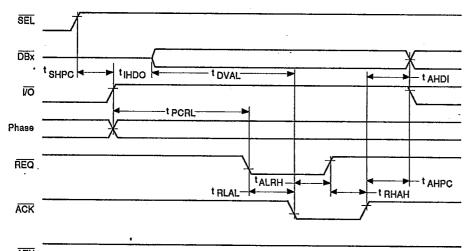
Symbol	Characteristic	Min	Max	Units
t _{SHPC}	SEL In High to Phase Change Out	100	. #	ns
t _{ILDO}	1/O Out Low to Data Out	800		ns
t _{DVRL}	Data Out Valid to REQ Out Low	∏55 🔭		ns
t _{PCRL}	Phase Change Out to REQ Our Low	500	4	ns
t _{RLAL}	REQ Out Low to ACR in Low	0		ns
t _{ALRH}	ACK in Low to REO Out High	0	175	ns
taldi (ACK in Low to Data Out Invalid	0		ns
t _{RHAH}	REC Out High to ACK In High	0		ns
t _{AHPC}	ACK In High to Phase Change Out	100		ns
t _{AHRL}	ACK In High to REQ Out Low	0	175	ns



ATN NOTE: Phase = signals that define the bus phase C/D, MSG

SEND ASYNCHRONOUS INFORMATION TRANSFER OUT (ACTING AS AN INITIATOR)

Symbo	I Characteristic	Min	Max	Units
t _{SHPC}	SEL In High to Phase Change In	0	~0	ns
t _{IHDO}	I/O In High to Data Out	A ST		ns
t _{PCRL}	Phase Change In to REQ In Low	400	LI D	ns
t _{rlal}	REQ In Low to ACK Out Low	1 0 1	175	ns
t _{DVAL}	Data Out Valid to ACK Out Low	55	•	ns
t _{ALRH}	ACK Out Low to REO In High	0		ns
t _{rhah}	REO In High to ACK Out High	0:	175	ns
t _{RHDI}	REQ In High to Data Out Invalid	0		ns
t _{AHPC}	ACK Out High to Phase Change In	0		ns



NOTE: Phase = signals that define the bus phase C/D, MSG

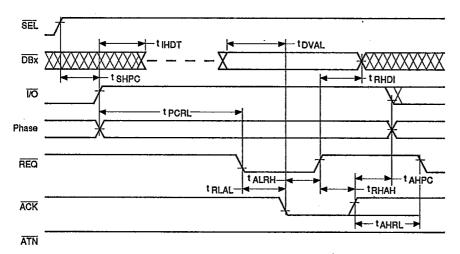
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RECEIVE ASYNCHRONOUS INFORMATION TRANSFER OUT (ACTING AS A TARGET)

Symbo	ol	Characteristic	Min	Max	Units	T 50 00
t _{SHPC}		SEL In High to Phase Change Out	100		ns	T-52-33-27
t _{IHDT}		I/O Out High to Data Bus TRISTATE	0-	4	ns	
t _{PCRL}		Phase Change to REQ Out Low	500 🥳	PER	ns	
t _{RLAL}		REQ Out Low to ACK In Low	(A)	M P	ns	
t _{DVAL}		Data In Valid to ACK In Low	0	A 13 .	ns	
t _{ALRH}		ACK In Low to REQ Out High	10	175	ns	
t _{RHDI}	4	REQ Out High to Data in Invalid	0	-	ns	
t _{RHAH}	F P	REO Out High to ACK in High	0		ns	
t _{AHPC}	13.00	ACK in High to Phase Change Out	0		ns	
t _{AHRL}	M	ACK In High to REQ Out Low	0	175	ns	



NOTE: Phase = signals that define the bus phase C/D, MSG

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RECEIVE SYNCHRONOUS INFORMATION TRANSFER IN (ACTING AS AN INITIATOR)

Symbol	Characteristic	Min	Max	Units
t _{DVRL}	Data Valid In to REQ In Low	0	- 4 月	ns
t _{RLDI}	REQ In Low to DATA Invalid	n 45 5		ns
t _{RLRH}	REQ In Low to REQ In High	50		ns
t _{RHRL}	REQ In Highto REQ In Low	50 17	3 2	ns
talah	ACK Out to Mito ACK Out High	Tcyc-10		ns
TAHAL T	ACK Out High to ACK Out Low	Tcyc-25		ns
t _{AHPC}	ACK Out High to Phase Change	0		ns

Parameters $t_{\rm SHPC}$, $t_{\rm ILDT}$, and $t_{\rm PCRL}$ are also applicable and are identical to those in Receive Asynchronous Information Transfer In (Acting as an Initiator), top of page 37.